



## (51) International Patent Classification:

H01L 21/3065 (2006.01) H01L 21/82 (2006.01)  
H01L 21/3205 (2006.01) H01L 21/98 (2006.01)  
H01L 21/324 (2006.01) H01L 21/56 (2006.01)  
H01L 21/46 (2006.01) H01L 23/28 (2006.01)

## (21) International Application Number:

PCT/SG2013/000305

## (22) International Filing Date:

23 July 2013 (23.07.2013)

## (25) Filing Language:

English

## (26) Publication Language:

English

## (30) Priority Data:

61/677,890 31 July 2012 (31.07.2012) US

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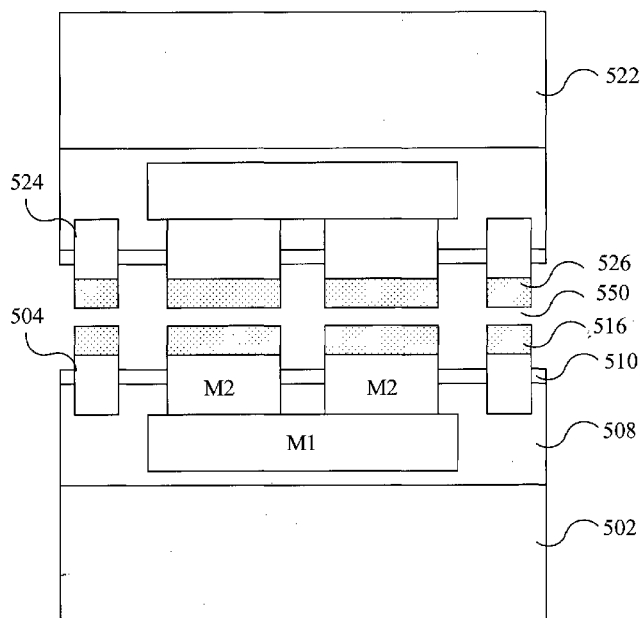
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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

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## (54) Title: SEMICONDUCTOR DEVICE AND METHOD FOR FORMING THE SAME



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(57) Abstract: In various embodiments, a method for forming a semiconductor device may be provided. The method may include providing a substrate. The method may also include forming a metal layer on the substrate. In addition, the method may include forming a first capping layer on the metal layer. The method may also include attaching the first capping layer to a second capping layer. The metal layer may comprise copper and a capping layer may comprise a metal nitride that has been activated in a plasma. The second capping layer may be disposed on a second substrate.

**WO 2014/021777 A1**



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**Published:**

— *with international search report (Art. 21(3))*